# Power MOSFET 20V, 125m $\Omega$ , 2A, Single N-Channel

This low-profile high-power MOSFET is produced using ON Semiconductor's trench technology, which is specifically designed to minimize gate charge and ultra low on resistance. This device is suitable for applications with low gate charge driving or ultra low on resistance requirements.

#### **Features**

- Low On-Resistance
- 1.8V drive
- ESD Diode-Protected Gate
- Pb-Free, Halogen Free and RoHS compliance
- Ultra small package SCH6 (1.6mm×1.6mm×0.56mmt)

# **Typical Applications**

• Load Switch

#### **SPECIFICATIONS**

#### **ABSOLUTE MAXIMUM RATING** at Ta = 25°C (Note 1)

Parameter	Symbol	Value	Unit
Drain to Source Voltage	VDSS	20	V
Gate to Source Voltage	VGSS	±12	٧
Drain Current (DC)	ID	2	Α
Drain Current (Pulse) PW ≤ 10µs, duty cycle ≤ 1%	IDP	8	Α
Power Dissipation When mounted on ceramic substrate (900mm²×0.8mm)	PD	0.8	W
Junction Temperature	Tj	150	°C
Storage Temperature	Tstg	-55 to +150	°C

Note 1: Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

#### THERMAL RESISTANCE RATINGS

Parameter	Symbol	Value	Unit			
Junction to Ambient When mounted on ceramic substrate (900mm² × 0.8mm)	$R_{\theta JA}$	156.2	°C/W			

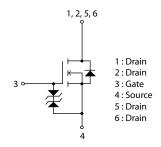


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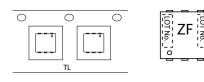
www.onsemi.com

VDSS	R <sub>DS</sub> (on) Max	ID Max
	125mΩ@ 4.5V	
20V	190mΩ@ 2.5V	2A
	310mΩ@ 1.8V	

# ELECTRICAL CONNECTION N-Channel



#### PACKING TYPE : TL MARKING



#### **ORDERING INFORMATION**

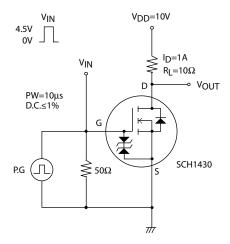
See detailed ordering and shipping information on page 5 of this data sheet.

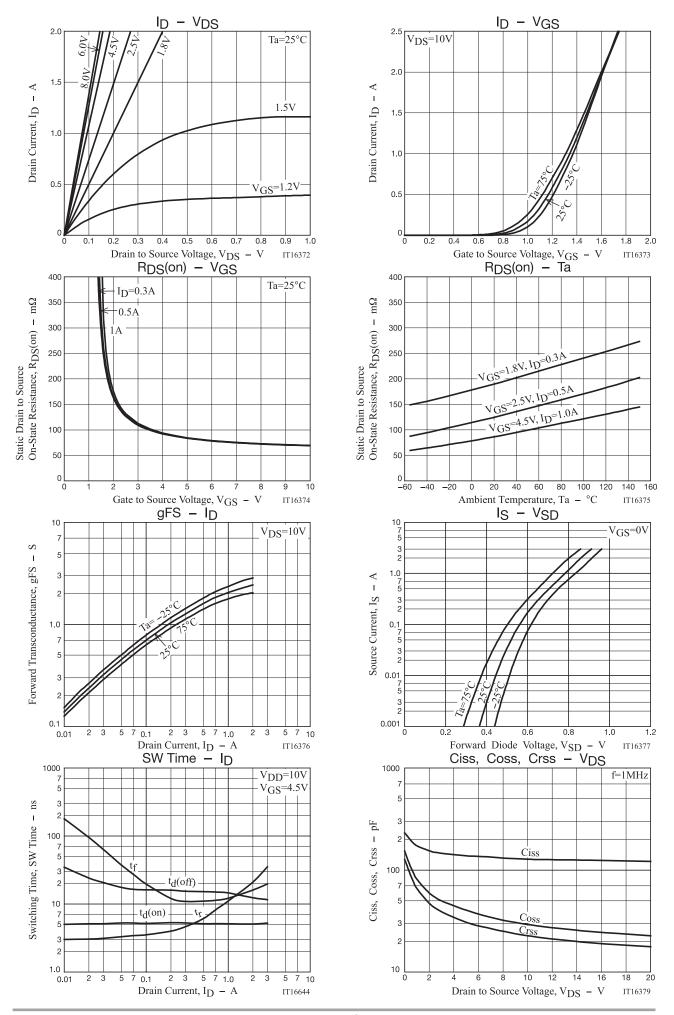
## **ELECTRICAL CHARACTERISTICS** at Ta = 25°C (Note 2)

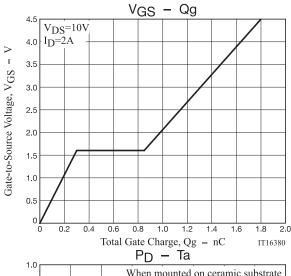
Parameter	Symbol	Conditions	Value			Unit	
Farameter	Syllibol	Symbol		typ	max	Offic	
Drain to Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	20			V	
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1	μΑ	
Gate to Source Leakage Current	IGSS	V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V			±10	μΑ	
Gate Threshold Voltage	V <sub>G</sub> S(th)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	0.4		1.3	V	
Forward Transconductance	gFS	V <sub>DS</sub> =10V, I <sub>D</sub> =1A		1.9		S	
	R <sub>DS</sub> (on)1	I <sub>D</sub> =1A, V <sub>GS</sub> =4.5V		93	125	mΩ	
Static Drain to Source On-State Resistance	R <sub>DS</sub> (on)2	I <sub>D</sub> =0.5A, V <sub>GS</sub> =2.5V		135	190	mΩ	
Resistance	R <sub>DS</sub> (on)3	I <sub>D</sub> =0.3A, V <sub>GS</sub> =1.8V		200	310	mΩ	
Input Capacitance	Ciss			128		pF	
Output Capacitance	Coss	V <sub>DS</sub> =10V, f=1MHz		28		pF	
Reverse Transfer Capacitance	Crss			21		pF	
Turn-ON Delay Time	t <sub>d</sub> (on)			5.1		ns	
Rise Time	tr			11		ns	
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit		14.5		ns	
Fall Time	tf			12		ns	
Total Gate Charge	Qg			1.8		nC	
Gate to Source Charge	Qgs	V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =2A		0.3		nC	
Gate to Drain "Miller" Charge	Qgd			0.55		nC	
Forward Diode Voltage	V <sub>SD</sub>	IS=2A, VGS=0V		0.85	1.2	V	

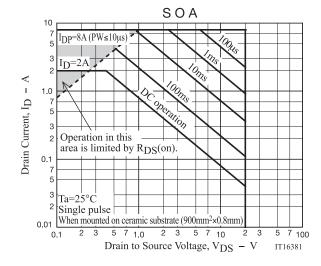
Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

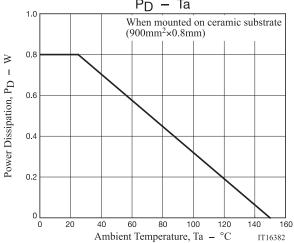
# **Switching Time Test Circuit**

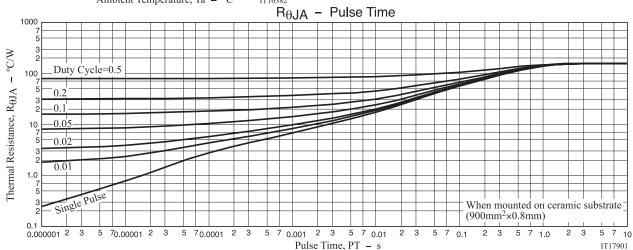






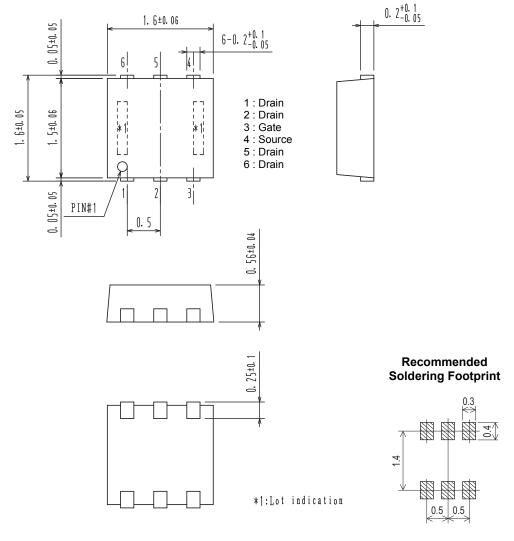






#### PACKAGE DIMENSIONS

unit: mm SOT-563 / SCH6 CASE 463AB ISSUE O



#### ORDERING INFORMATION

Device	Marking	Package	Shipping (Qty / Packing)	
SCH1430-TL-H	75	SOT-563 / SCH6	5 000 / Tana & Dani	
SCH1430-TL-W	I30-TL-W		5,000 / Tape & Reel	

<sup>†</sup> For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. http://www.onsemi.com/pub\_link/Collateral/BRD8011-D.PDF

Note on usage: Since the SCH1430 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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